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INFORMATION DISCLOSURE
STATEMENT BY APPLICANTAPPLICANT
FUJISAKI et al

(Use several sheets if necessary)

FILING DATE
July 23, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SWL	4	5	4	4	4	1	7	10/85	Clarke			
	4	6	1	8	3	9	6	10/86	Shimoda			
	3	8	3	3	3	4	2	9/74	Holliday			
	3	4	4	6	6	0	3	5/69	Lolacono			
	3	0	3	3	6	6	0	5/62	Okkerse			
	4	2	9	9	6	5	0	11/81	Bonner			
	2	9	0	8	0	0	4	10/59	Levinson			
	4	5	3	9	0	6	7	9/85	Washizuka			
	4	5	8	6	9	7	9	5/86	Katsumata			
	4	6	3	7	8	5	4	1/87	Fukuda			
SWC	4	6	4	5	5	6	0	2/87	Matsumoto			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
SWC	55 1 1 3 6 9 9	9/80	Japan			X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWL	Ghandhi, S. VLSI Fabrication Principles, John Wiley, 1983 pp 86-90, 98-100
SWL	Sze, S., Physics of Semiconductor Devices, John Wiley, 1981, p 33
SWC	IEEE Transactions on Electron Devices, vo. ED-31, No. 8, Aug. 1984, pp 1057, para 4 5; New York, US; S. Miyazawa

EXAMINER	CRANE	DATE CONSIDERED	6/2004
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWL	Journal of Crystal Growth, Vol. 63 no. 2, Oct. 1983 pp 415-418, Amsterdam NL; Fornari "Dislocation-free silicon-doped gallium arsenide grown by LEC Procedure
	Terashima "Control of Growth Parameters for Obtaining Highly Uniform Large Diameter LEC GaAs" 5th Conf. On Semi-insulating III-V Materials, 1988 pp 413-422
	Matsuoka et al "uniformity Evaluation of MESFETs for FGaAs LSI Fabrication" IEEE Trans. On Elec. Dev. Vol ED31, no. 8 Aug. 1984 pp 1062
	Applied Physics Letters, vol 44, no. 1, Jan. 1984 pp 74-76 New York, US; Hunter "Carbon in Semi-Insulating, liquid Encapsulated Czochralski GaAs"
SWL	Patent Abstracts of Japan, vol. 4,no. 173 (C-32) [655], 29 Nov. 1980; JP A-55-113-669 Sumitomo 2-09-1980

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